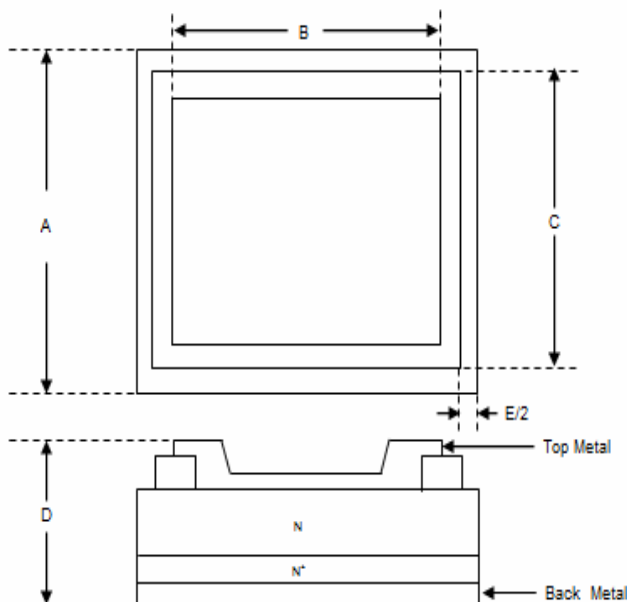


Planar MOS-Controlled Diode Wafer (PMCD)



Item	Dimensions	
	um	mil
Die Size (A)	2581	101.6
Top Metal Pad Size (B)	2374	93.5
Passivation Seal (C)	2511	98.8
Wafer Thickness (D)	260	10.2
Scribe Line Width (E)	70	2.76
Other Informations		
Wafer Size	6"	
Gross Die	2360	
Top Metal	Ag	
Back Metal	Ag	

Electrical Characteristics @TA=25°C

Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.05mA	V_{RRM}	300	315	V
Maximum Average Forward Rectified Current	I_O	15	-	A
Forward Voltage Drop, @ $I_F=3A$ @ $I_F=10A$ @ $I_F=15A$	V_F	- 0.89 0.95	0.78 - -	V
Maximum Reverse Current at Rated V_{RRM}	I_R	1	0.5	μA
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	250	-	A
Operating Temperature Range	T_J	-50 to +175	-	°C
Storage Temperature Range	T_{STG}	-50 to +175	-	°C